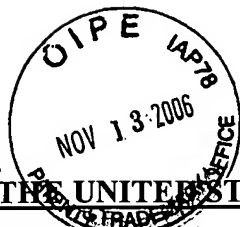


S/N 10/789,042



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Examiner: N. D. Richards

Serial No.: 10/789,042

Group Art Unit: 2815

Filed: February 27, 2004

Docket: 1303.050US2

Title: LaAlO₃ FILMS (as amended)

COMMUNICATION CONCERNING RELATED APPLICATIONS

MS AF

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related applications in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date/Issue Date</u>	<u>Attorney Docket</u>	<u>Title</u>
11496196	July 31, 2006	1303.068US4	MEMORY UTILIZING OXIDE-CONDUCTOR NANOLAMINATES
10443021 6970053	May 22, 2003	1303.137US1	ATOMIC LAYER DEPOSITION (ALD) HIGH PERMEABILITY LAYERED MAGNETIC FILMS TO REDUCE NOISE IN HIGH SPEED INTERCONNECTION
11063132	February 22, 2005	1303.137US2	HIGH PERMEABILITY LAYERED MAGNETIC FILMS TO REDUCE NOISE IN HIGH SPEED INTERCONNECTION (As Amended)
11140643	May 27, 2005	1303.141US1	HAFNIUM TITANIUM OXIDE FILMS
11152759	June 14, 2005	1303.144US1	IRIDIUM / ZIRCONIUM OXIDE STRUCTURE
11459792	July 25, 2006	1303.092US2	ZrAlxOy DIELECTRIC LAYERS
11297567	December 8, 2005	1303.157US1	LANTHANIDE YTTRIUM ALUMINUM OXIDE DIELECTRIC FILMS
11297741	December 8, 2005	1303.161US1	HAFNIUM TANTALUM TITANIUM OXIDE FILMS
11427569	June 29, 2006	1303.079US2	LANTHANIDE DOPED TiOX DIELECTRIC FILMS
11493074	July 26, 2006	1303.101US3	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS
11493112	July 26, 2006	1303.114US2	ZIRCONIUM-DOPED TANTALUM OXIDE FILMS

COMMUNICATION CONCERNING RELATED APPLICATIONS

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11457978	July 17, 2006	1303.061US4	ATOMIC LAYER DEPOSITED NANOLAMINATES OF HfO ₂ /ZrO ₂ FILMS AS GATE DIELECTRICS
11457987	July 17, 2006	1303.061US5	ATOMIC LAYER DEPOSITED NANOLAMINATES OF Hf O ₂ /ZrO ₂ FILMS AS GATE DIELECTRICS
11584229	October 20, 2006	1303.126US2	LANTHANUM HAFNIUM OXIDE DIELECTRICS
11528776	September 28, 2006	1303.130US2	ATOMIC LAYER DEPOSITION OF CeO ₂ /Al ₂ O ₃ FILMS AS GATE DIELECTRICS

Continuations and divisionals may be later filed on the cases listed above, or cited to the Examiner in any previous Communication Concerning Related Applications. Applicants request that the Examiner review all continuations and divisionals of the above-listed or previously-cited patent applications before allowing the claims of the present patent application.

Respectfully submitted,

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By Applicants' Representatives,

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Date 6 November 2006 By David R. Cochran
David R. Cochran
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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS AF, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 6 th day of November, 2006.

David R. Cochran
Name

David R. Cochran
Signature